



## 1. Description

SS12N10NSL, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, and improve switching performance. This is suitable device for synchronous rectifier and high speed switching applications.

### KEY CHARACTERISTICS

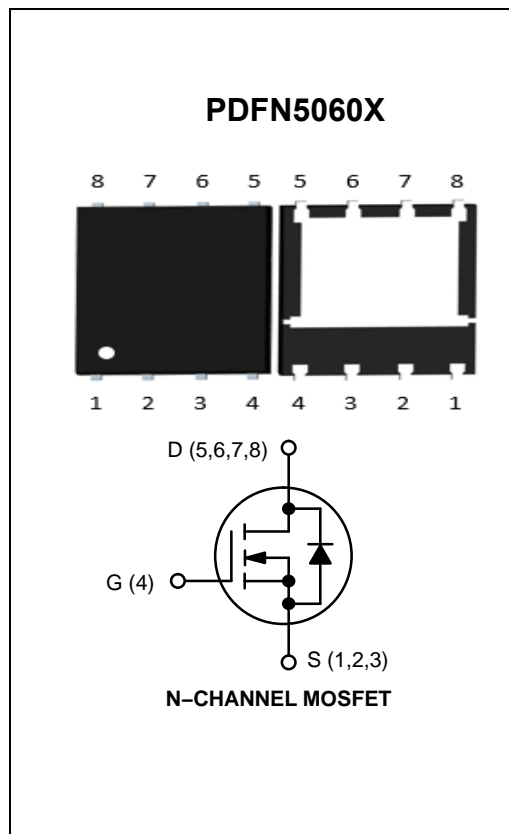
Parameter	Value	Unit
V <sub>DSS</sub>	100	V
I <sub>D</sub>	58	A
R <sub>DS(on)</sub> typ.	10	mΩ

### FEATURES

- Fast Switching
- Low On-Resistance (  $R_{DS(on)} \leq 12\text{m}\Omega$  )
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

### APPLICATIONS

- Switching applications
- Synchronous rectifier



### ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS12N10NSL	PDFN5*6	SS12N10NSL	Reel